Jun-shuai Li

List of Publications by Year
in descending order

31	371	840776	794594
papers	citations	11 h-index	19 g-index

31	31	31	533
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Breakdown Enhancement and Current Collapse Suppression by High-Resistivity GaN Cap Layer in Normally-Off AlGaN/GaN HEMTs. IEEE Electron Device Letters, 2017, 38, 1567-1570.	3.9	81
2	Formation Mechanism and Optical Properties of InAs Quantum Dots on the Surface of GaAs Nanowires. Nano Letters, 2012, 12, 1851-1856.	9.1	36
3	Annealing effects on properties of Ga2O3 films deposited by plasma-enhanced atomic layer deposition. Materials Letters, 2019, 237, 105-108.	2.6	31
4	Growth and photoluminescence of InxGa1â^'xAs quantum dots on the surface of GaAs nanowires by metal organic chemical vapor deposition. Applied Physics Letters, 2012, 101, .	3.3	23
5	Fabrication and optical properties of GaAs/InGaAs/GaAs nanowire coreâ€“multishell quantum well heterostructures. Nanoscale, 2015, 7, 1110-1115.	5.6	23
6	Anomalous photoconductive behavior of a single InAs nanowire photodetector. Applied Physics Letters, 2015, 107, .	3.3	22
7	Metalorganic Chemical Vapor Deposition Heteroepitaxial Î²â€Ga₂O₃ and Black Phosphorus Pn Heterojunction for Solarâ€Blind Ultraviolet and Infrared Dualâ€Band Photodetector. Physica Status Solidi (A) Applications and Materials Science, 2020, 217, 1900861.	1.8	17
8	Self-catalyzed growth of pure zinc blende âŸ¨110âŸ© InP nanowires. Applied Physics Letters, 2015, 107, .	3.3	16
9	Axially connected nanowire core-shell p-n junctions: a composite structure for high-efficiency solar cells. Nanoscale Research Letters, 2015, 10, 22.	5.7	15
10	Self-catalyzed metal organic chemical vapor deposition growth of vertical Î²-Ga₂O₃ nanowire arrays. Nanotechnology, 2020, 31, 02LT01.	2.6	14
11	Inductively coupled plasma etching of GaAs in Cl 2 /Ar, Cl 2 /Ar/O 2 chemistries with photoresist mask. Applied Surface Science, 2015, 356, 776-779.	6.1	11
12	Influence of pressure on the properties of AlN deposited by DC reactive magnetron sputtering on Si (100) substrate. Micro and Nano Letters, 2019, 14, 146-149.	1.3	11
13	Realization of Stranskiâ€“Krastanow InAs quantum dots on nanowire-based InGaAs nanoshells. Journal of Materials Chemistry C, 2013, 1, 7914.	5.5	9
14	Controllable Ga catalyst deposition on GaN template and fabrication of ordered vertical Î²-Ga2O3 nanowire array. Journal Physics D: Applied Physics, 2020, 53, 305103.	2.8	9
15	Growth of InAs quantum dots on Si-based GaAs nanowires by controlling the surface adatom diffusion. Journal of Crystal Growth, 2013, 384, 82-87.	1.5	7
16	Analysis of critical dimensions for axial double heterostructure nanowires. Journal of Applied Physics, 2012, 112, .	2.5	5
17	Growth and characterization of GaAs/InxGa1â^'xAs/GaAs axial nanowire heterostructures with symmetrical heterointerfaces. Chinese Physics B, 2013, 22, 066101.	1.4	5
18	Controlled lateral epitaxial growth in vertical Î²-Ga2O3 nanowires on sapphire by MOCVD. Journal Physics D: Applied Physics, 2021, 54, 305101.	2.8	5

#	Article	IF	Citations
19	Growth of Self-Catalyzed InP Nanowires by Metalorganic Chemical Vapour Deposition. Chinese Physics Letters, 2012, 29, 126102.	3.3	4
20	First-principle calculations of dilute nitride GaP1â˜'xNx alloy in zinc-blende structures. Physica B: Condensed Matter, 2012, 407, 112-115.	2.7	4
21	Growth and characterization of straight InAs/GaAs nanowire heterostructures on Si substrate. Chinese Physics B, 2013, 22, 076102.	1.4	4
22	Morphological and temperature-dependent optical properties of InAs quantum dots on GaAs nanowires with different InAs coverage. Applied Physics Letters, 2013, 103, .	3.3	4
23	Fabrication and electrical properties of axial and radial GaAs nanowire pn junction diode arrays. Chinese Physics B, 2014, 23, 128503.	1.4	3
24	Controllable growth and optical properties of InP and InP/InAs nanostructures on the sidewalls of GaAs nanowires. Journal of Applied Physics, 2014, 116, 214304.	2.5	3
25	Fabrication and optical properties of multishell InAs quantum dots on GaAs nanowires. Journal of Applied Physics, 2015, 117, 054301.	2.5	3
26	Growth and characterization of InAs quantum dots on InP nanowires with zinc blende structure. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2013, 31, .	1.2	2
27	Preadsorption of gallium on GaAs(111)B surface during the self-catalyst growth of GaAs nanowires. Physica B: Condensed Matter, 2014, 452, 31-36.	2.7	2
28	Fabrication and optical properties of typeâ€II InP/InAs nanowire/quantumâ€dot heterostructures. Physica Status Solidi - Rapid Research Letters, 2016, 10, 168-171.	2.4	2
29	VLS growth of GaAs/InGaAs/GaAs axial double-heterostructure nanowires. , 2011, , .		0
30	Growth of Axial GaAs Nanowire PN and PIN Junctions. , 2012, , .		0
31	A Single InP Nanowire Room-Temperature Photodetector. , 2015, , .		0